

Aneta Drabińska

List of Publications by Year in descending order

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592
citing authors

#	ARTICLE	IF	CITATIONS
1	Strain control in graphene on GaN nanowires: Towards pseudomagnetic field engineering. Carbon, 2022, 186, 128-140.	5.4	1
2	Volumetric incorporation of NV diamond emitters in nanostructured F2 glass magneto-optical fiber probes. Carbon, 2022, 196, 10-19.	5.4	11
3	Properties of graphene deposited on GaN nanowires: influence of nanowire roughness, self-induced nanogating and defects. Beilstein Journal of Nanotechnology, 2021, 12, 566-577.	1.5	3
4	Highly effective gating of graphene on GaN. Applied Surface Science, 2021, 560, 149939.	3.1	3
5	Mechanism of Iodine(III)-Promoted Oxidative Dearomatizing Hydroxylation of Phenols: Evidence for a Radical-Chain Pathway. Chemistry - A European Journal, 2020, 26, 11584-11592.	1.7	15
6	Surface-enhanced Raman scattering in graphene deposited on Al Ga ¹⁻ⁿ N/GaN axial heterostructure nanowires. Applied Surface Science, 2019, 475, 559-564.	3.1	7
7	Surface-enhanced Raman scattering of graphene caused by self-induced nanogating by GaN nanowire array. Carbon, 2018, 128, 70-77.	5.4	8
8	Radiative recombination and other processes related to excess charge carriers, decisive for efficient performance of electronic devices. Lithuanian Journal of Physics, 2018, 58, .	0.1	5
9	High-spin configuration of Mn in Bi ₂ Se ₃ three-dimensional topological insulator. Journal of Magnetism and Magnetic Materials, 2016, 419, 301-308.	1.0	8
10	Fe dopant in ZnO: 2+ versus 3+ valency and ion-carrier exchange interaction. Physical Review B, 2016, 94, .	0.1	18
11	Toward Better Efficiency of Air-Stable Polyazomethine-Based Organic Solar Cells Using Time-Resolved Photoluminescence and Light-Induced Electron Spin Resonance as Verification Methods. Journal of Physical Chemistry C, 2016, 120, 11415-11425.	1.5	24
12	g-factors of conduction electrons and holes in B ₂ S ₂	1.1	29
13	Enhanced Raman scattering and weak localization in graphene deposited on GaN nanowires. Physical Review B, 2015, 92, .	1.1	9
14	Electron scattering in graphene with adsorbed NaCl nanoparticles. Journal of Applied Physics, 2015, 117, 014308.	1.1	3
15	Optical and Electrical Studies of Graphene Deposited on GaN Nanowires. Acta Physica Polonica A, 2014, 126, 1087-1089.	0.2	0
16	ESR Spectroscopy of Graphene with Adsorbed NaCl Particles. Acta Physica Polonica A, 2014, 126, 1187-1189.	0.2	1
17	Application of microwave spectroscopy to studies of electron transport properties. Journal of Crystal Growth, 2014, 401, 314-318.	0.7	2
18	Multilayer graphene stacks grown by different methods-thickness measurements by X-ray diffraction, Raman spectroscopy and optical transmission. Crystallography Reports, 2013, 58, 1053-1057.	0.1	6

#	ARTICLE	IF	CITATIONS
19	Microwave studies of weak localization and antilocalization in epitaxial graphene. , 2013, , .		1
20	Three-dimensional topological insulators Bi_2Te_3 , Bi_2Se_3 , and $\text{Bi}_2\text{Te}_2\text{Se}$ - a microwave spectroscopy study. , 2013, , .		4
21	Enhancement of elastic and inelastic scattering lengths in quasi-free-standing graphene measured with contactless microwave spectroscopy. <i>Physical Review B</i> , 2013, 88, .	1.1	9
22	Contactless microwave studies of weak localization in epitaxial graphene. <i>Physical Review B</i> , 2012, 86, .	1.1	10
23	Landau-Level Spectroscopy of Relativistic Fermions with Low Fermi Velocity in the Bi_2Te_3 Topological Insulator. <i>Physical Review Letters</i> . 2012, 109, 247604.	2.9	23
24	Pinned and unpinned epitaxial graphene layers on SiC studied by Raman spectroscopy. <i>Journal of Applied Physics</i> , 2012, 111, .	1.1	14
25	Electron spin resonance and Rashba field in GaN-based materials. <i>Physica B: Condensed Matter</i> , 2011, 406, 2548-2554.	1.3	11
26	Growth kinetics of epitaxial graphene on SiC substrates. <i>Physical Review B</i> , 2010, 81, .	1.1	26
27	Electroreflectance investigations of quantum confined Stark effect in GaN quantum wells. <i>Journal of Physics: Conference Series</i> , 2010, 253, 012009.	0.3	0
28	Tunable GaN/AlGaN ultraviolet detectors with built-in electric field. <i>Journal of Applied Physics</i> , 2009, 105, .	1.1	30
29	Electroreflectance spectroscopy on InGaN quantum wells. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009, 206, 816-820.	0.8	2
30	Optical Absorption and Raman Scattering Studies of Few-Layer Epitaxial Graphene Grown on 4H-SiC Substrates. <i>Acta Physica Polonica A</i> , 2009, 116, 835-837.	0.2	5
31	InGaN QW in External Electric Field Controlled by Pumping of 2D-Electron Gas. <i>Acta Physica Polonica A</i> , 2008, 114, 1179-1186.	0.2	3
32	Electroreflectance and photorefectance spectra of tricolor III-nitride detector structures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007, 204, 459-465.	0.8	6
33	Multiband GaN/AlGaN UV Photodetector. <i>Acta Physica Polonica A</i> , 2006, 110, 211-217.	0.2	6
34	Electroreflectance and photorefectance studies of AlGaN/GaN heterostructure with a QW placed inside AlGaN layer. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005, 202, 1308-1312.	0.8	3
35	Investigation of 2D Electron Gas on AlGaN/GaN Interface by Electroreflectance. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003, 0, 329-333.	0.8	9
36	Tuning of Spectral Sensitivity of AlGaN/GaN UV Detector. <i>Acta Physica Polonica A</i> , 2003, 103, 675-681.	0.2	8

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37	Photo- and Electroreflectance Spectroscopy of Low-Dimensional III-Nitride Structures. Acta Physica Polonica A, 2003, 104, 149-164.	0.2	12
38	Optical determination of the dopant concentration in the $\hat{\Gamma}$ -doping layer. Journal of Applied Physics, 2002, 92, 163-167.	1.1	5
39	Determination of Si δ -Doping Concentration in GaN by Electroreflectance. Physica Status Solidi (B): Basic Research, 2002, 234, 868-871.	0.7	3
40	Growth Rate and Thickness Uniformity of Epitaxial Graphene. Materials Science Forum, 0, 645-648, 569-572.	0.3	7
41	Optical Transmission of Epitaxial Graphene Layers on SiC in the Visible Spectral Range. Materials Science Forum, 0, 645-648, 615-618.	0.3	3